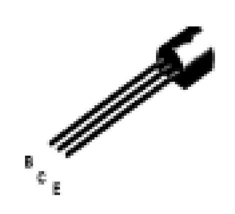
NPN TRANSISTOR **C945**

100mA



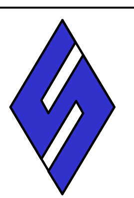
- AF OUTPUT AMPLIFIER

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS（Ta=25℃）

PARAMETERS	SYMBOL	MIN	TYP	MAX	UNIT	CONDITION
Collector-Emitter Breakdown Voltage	BVceo	50			V	Ic=1mA
Collector-Base Breakdown Voltage	BVcbo	60			V	Ic=5*u*A
Emitter-Base Breakdown Voltage	BVebo	5			V	Ie=50 μ A
Collector-Base Leakage	Icbo			0.1	*u*A	Vcb=60V
Emitter-Base Leakage	Iebo			0.1	*u*A	Veb=5V
Collector-Emitter Saturation Voltage	Vce（sat）		0.18	0.3	V	Ic=100mA, Ib=10mA
DC Current Gain	Hfe	90	200	600		Vce=6.0V,Ic=1.0mA
Collector Current	Ic		100		mA	
Current Gain Bandwidth	f_T	100	180		MHz	Vce=6V, Ie=10mA
Output Capacitance	Cob		4.5	6.0	pF	Vcb=10V,Ie=0,f=1MHz
Power Dissipation	Pc			0.25	W	
Junction Temperature	Tj			125	℃	
Storage Temperature	Tstg	-55		125	℃	

Classification of Hfe

Rank	R	Q	P	K
Range	90-180	135-270	200-400	300-600



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